# Problems for Physik der Materie III

#### Due by June 26, 2019

## Series 9: Fermi surface of a metal, Ewald construction, and intrinsic semiconductors

#### 9.1 Fermi surface of gold

The periodicity observed in the de Haas-van Alphen effect is linked to an extremal cross-sectional area  $A_k$  of the Fermi surface, which is perpendicular to **B**.

- (a) Assuming that Au can be approximated by a three-dimensional free electron Fermi gas, estimate the extremal area  $A_k$  of the Fermi surface using an electron density of  $n_{el}^{Au} = 5.90 \times 10^{22} \,\mathrm{cm}^{-3}$ .
- (b) From the equality of centrifugal and Lorentz forces for free electrons in a magnetic field, derive a relation between the "radii" of the extremal orbits in real and reciprocal space. Using the result of (a), calculate the extremal area  $A_r$  in real space for Au in a field B of 1 T.
- (c) Experiments on Au show an oscillation period of  $\Delta(1/B) = 1.95 \times 10^{-5} \,\mathrm{T}^{-1}$ along the [001]-direction and a superposition of two periods of  $2.05 \times 10^{-5} \,\mathrm{T}^{-1}$ and  $6.0 \times 10^{-4} \,\mathrm{T}^{-1}$  along the [111]-direction. Calculate the corresponding extremal areas  $A_k$  in k-space and discuss the re-

Calculate the corresponding extremal areas  $A_k$  in k-space and discuss the results in terms of the "real" Fermi surface shown in Fig. 1.



Figure 1: Fermi surface of gold

## 9.2 Ewald construction

X-rays with an energy of 7 keV are used to analyze a simple orthorhombic lattice (a = 0.6, b = 0.8, c = 0.4 nm). The x-rays propagate in the (001) plane and also the detector scans in the (001) plane. The crystal is being rotated around the  $\langle 001 \rangle$  direction. Sketch the Ewald construction for this scenario. Determine the number and the scattering angles of the scattered beams using a computer and a programming language of your choice.

## 9.3 Conductivity of an intrinsic semiconductor

Consider an intrinsic Ge crystal at liquid nitrogen temperature (T = 77 K). Assume an average electron carrier concentration  $n = 10^{12}$  cm<sup>-3</sup> due to optical excitation across the band gap. At this temperature, the mobilities of electrons and holes are assumed to be the same with  $\mu_n = \mu_p = \mu \approx 5 \times 10^3$  cm<sup>2</sup>/Vs.

Determine the electrical conductivity  $\sigma$  and, for a cube of an edge length of 1 cm, the current I between two opposite faces at a voltage of 100 V.